Standard specifications of 100 mm Sn-doped β-Ga_2O_3 (001) substrate

Items		Specifications
Orientation		(001)
Dopant		Sn
Conductivity		n-type
Resistivity (Ω·cm)		0.007–0.042
Dimensions	Diameter (mm)	100 ±0.5
	Orientation flat width (mm)	32.5 ±2.5
	Index flat width (mm)	18.0 ±2.5
	Thickness (mm)	0.65 ±0.02
	Reference	Fig. 1
Offset angle (degree)		[010]:0 ±1
		[100]:0 ±1
FWHM (arcsec)		[010]:50 or less
		[100]:50 or less
Surface	Front	CMP
	Back	CMP

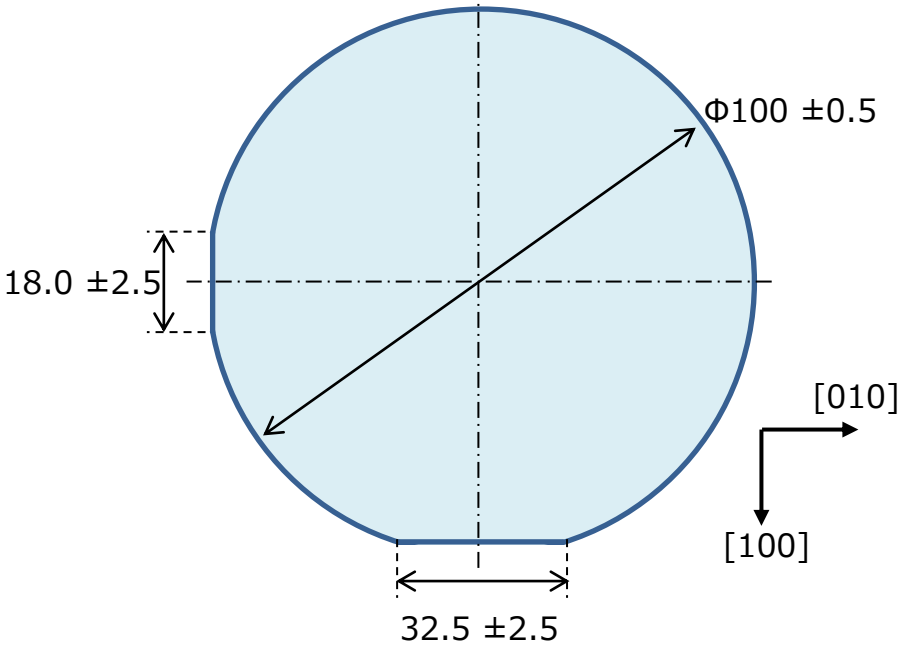

Fig. 1

Remarks
1 There are cases in which the opposite side of OF is chipped less than 18 mm.
2 There are cases in which the OF side is chipped less than 32.5 mm ±2.5 mm.
3 These products must be used for research and development purposes only.
4 The substrates must not be used as a seed crystal.
5 The specifications are subject to change without notice.

Novel Crystal Technology, Inc.

2024.7. 29

Standard specifications of 2 inch Sn-doped β-Ga_2O_3 (001) substrate

Items		Specifications
Orientation		(001)
Dopant		Sn
Conductivity		n-type
Resistivity (Ω·cm)		0.007–0.042
Dimensions	Diameter (mm)	50.8 ±0.3
	Orientation flat width (mm)	15.9 ±2.5
	Index flat width (mm)	8.0 ±2.5
	Thickness (mm)	0.65 ±0.02
	Reference	Fig. 2
Offset angle (degree)		[010]:0 ±1
		[100]:0 ±1
FWHM (arcsec)		[010]:50 or less
		[100]:50 or less
Surface	Front	CMP
	Back	CMP

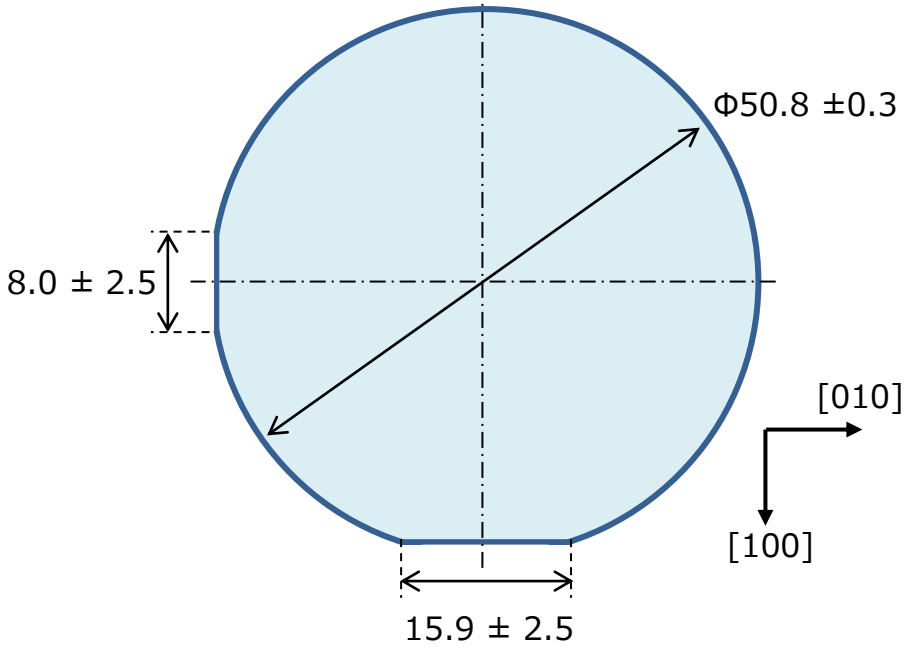

Fig.2

Remarks
1 There are cases in which the opposite side of OF is chipped less than 8 mm.
2 There are cases in which the OF side is chipped less than 15.9 mm ±2.5 mm.
3 These products must be used for research and development purposes only.
4 The substrates must not be used as a seed crystal.
5 The specifications are subject to change without notice.

Novel Crystal Technology, Inc.

2024.7. 29

Standard specifications of 10×15 mm² β-Ga_2O_3 (010) substrates

Items		Specifications		
Orientation		(010)		
Dopant		Sn	Undoped	Fe
Conductivity		n-type	n-type	Insulating ($>10^{10}\Omega\cdot$cm)
*N*d-*N*a (cm^{-3})		1×10^{18}–9×10^{18}	≦9×10^{17}	-
Dimensions	A-B (mm)	15 ±0.3	15 ±0.3	15 ±0.3
	C-D (mm)	10 ±0.3	10 ±0.3	10 ±0.3
	Thickness (mm)	0.5 ±0.02	0.5 ±0.02	0.5 ±0.02
	Reference	Fig. 3	Fig. 3	Fig. 3
Offset angle (degree)		⊥[102]:0 ±1	⊥[102]:0 ±1	⊥[102]:0 ±1
		[102]:0 ±1	[102]:0 ±1	[102]:0 ±1
FWHM (arcsec)		⊥[102]:150 or less	⊥[102]:150 or less	⊥[102]:150 or less
		[102]:150 or less	[102]:150 or less	[102]:150 or less
Surface	Front	CMP	CMP	CMP
	Back	Grinding	Grinding	Grinding

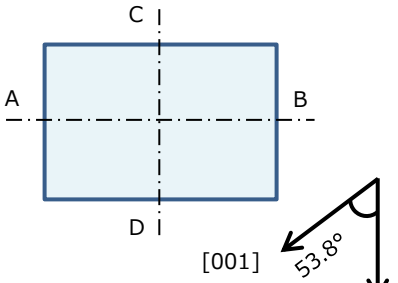

Fig. 3

Remarks

1 These products must be used for research and development purposes only.
2 The substrates must not be used as a seed crystal.
3 The specifications are subject to change without notice.

Novel Crystal Technology, Inc.

Standard specifications of 2 inch β-Ga_2O_3 ($\bar{2}01$) substrates

Items		Specifications		
Orientation		($\bar{2}01$)		
Dopant		Sn	Undoped	Fe
Conductivity		n-type	n-type	Insulating ($>10^{10}\Omega\cdot$cm)
*N*d-*N*a (cm^{-3})		1×10^{18}–2×10^{19}	≦9×10^{17}	-
Dimensions	Diameter (mm)	50.8 ±0.3	50.8 ±0.3	50.8 ±0.3
	Orientation flat width (mm)	15.9 ±2.5	15.9 ±2.5	15.9 ±2.5
	Thickness (mm)	0.68 ±0.02	0.68 ±0.02	0.68 ±0.02
	Reference	Fig. 4	Fig. 4	Fig. 4
Offset angle (degree)		[010]: 0 ±0.4	[010]: 0 ±0.4	[010]:0 ±1
		[102]:-0.7 ±0.4	[102]:-0.7 ±0.4	[102]:-0.7 ±1
FWHM (arcsec)		[010]:150 or less	[010]:150 or less	[010]:150 or less
		[102]:150 or less	[102]:150 or less	[102]:150 or less
Surface	Front	CMP	CMP	CMP
	Back	Grinding	Grinding	Grinding

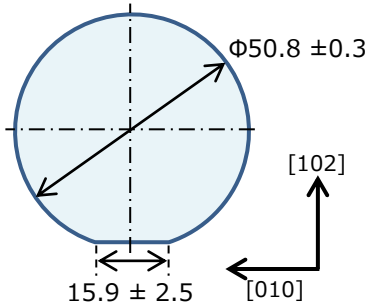

Fig. 4

Remarks
1 There are cases in which the opposite side of OF is chipped less than 8 mm.
2 There are cases in which the OF side is chipped less than 15.9 mm ±2.5 mm.
3 These products must be used for research and development purposes only.
4 The substrates must not be used as a seed crystal.
5 The specifications are subject to change without notice.

Novel Crystal Technology, Inc.

2024.7. 29